# DATA SHEET

Solid State Relay OCMOS FET

PS7111-2A,PS7111L-2A

# 8-PIN DIP, 100 V BREAK DOWN VOLTAGE 2-ch Optical Coupled MOS FET

# DESCRIPTION

NEC

The PS7111-2A and PS7111L-2A are solid state relays containing GaAs LEDs on the light emitting side (input side) and MOS FETs on the output side.

They are suitable for analog signal control because of their low offset and high linearity.

The PS7111L-2A has a surface mount type lead.

# **\*** FEATURES

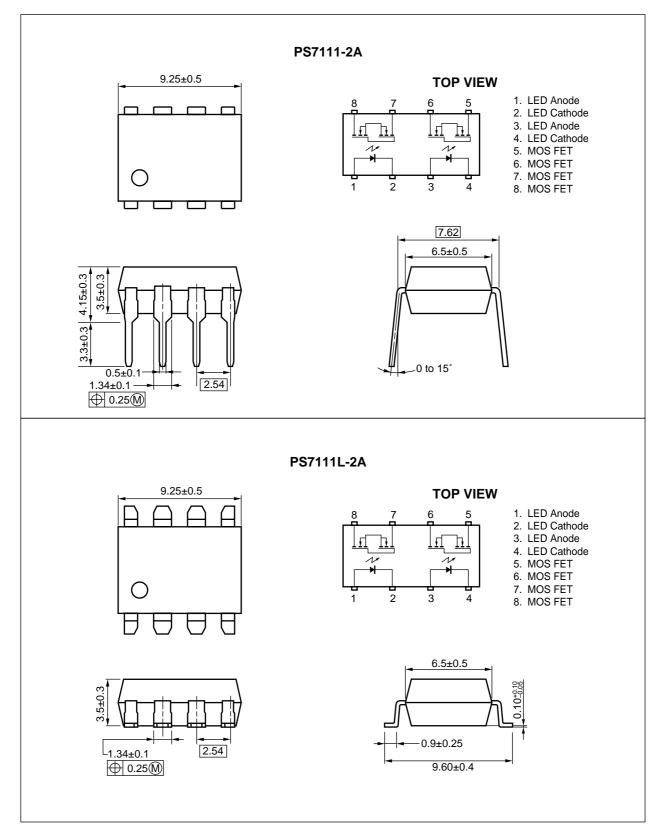
- 2 channel type (1 a + 1 a output)
- Low LED operating current (IF = 2 mA)
- Designed for AC/DC switching line changer
- Small package (8-pin DIP)
- · Low offset voltage
- PS7111L-2A: Surface mount type
- UL approved: File No. E72422 (S)
- BSI approved: No. 8245/8246
- CSA approved: No. CA 101391

# APPLICATIONS

- Exchange equipment
- Measurement equipment
- FA/OA equipment

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# PACKAGE DIMENSIONS (in millimeters)



# **\*** ORDERING INFORMATION

Part Number	Package	Packing Style	Application Part Number <sup>*1</sup>
PS7111-2A	8-pin DIP	Magazine case 50 pcs	PS7111-2A
PS7111L-2A			PS7111L-2A
PS7111L-2A-E3		Embossed Tape 1 000 pcs/reel	
PS7111L-2A-E4			

\*1 For the application of the Safety Standard, following part number should be used.

# ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit	
Diode	Forward Current (DC)	lF	50	mA	
	Reverse Voltage	VR	5.0	V	
	Power Dissipation	PD	50	mW/ch	
	Peak Forward Current <sup>*1</sup>	IFP	1	А	
MOS FET	IOS FET Break Down Voltage		100	V	
	Continuous Load Current	١L	100	mA	
	Pulse Load Current <sup>*2</sup> (AC/DC Connection)	Ilp	300	mA	
	Power Dissipation	PD	375	mW/ch	
Isolation Voltage <sup>*3</sup>		BV	1 500	Vr.m.s.	
Total Power Dissipation		Ρτ	850	mW	
Operating Ambient Temperature		TA	-40 to +80	°C	
Storage Temperature		Tstg	-40 to +100	°C	

\*1 PW = 100  $\mu$ s, Duty Cycle = 1 %

\*2 PW = 100 ms, 1 shot

\*3 AC voltage for 1 minute at TA = 25 °C, RH = 60 % between input and output

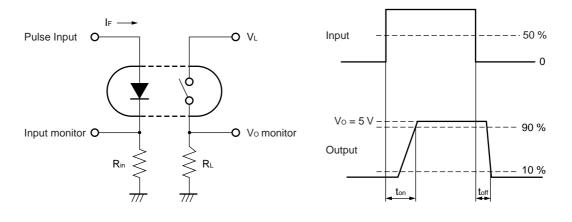
# **RECOMMENDED OPERATING CONDITIONS (TA = 25 °C)**

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	
LED Operating Current	lF	2	10	20	mA	
LED Off Voltage	VF	0		0.5	V	

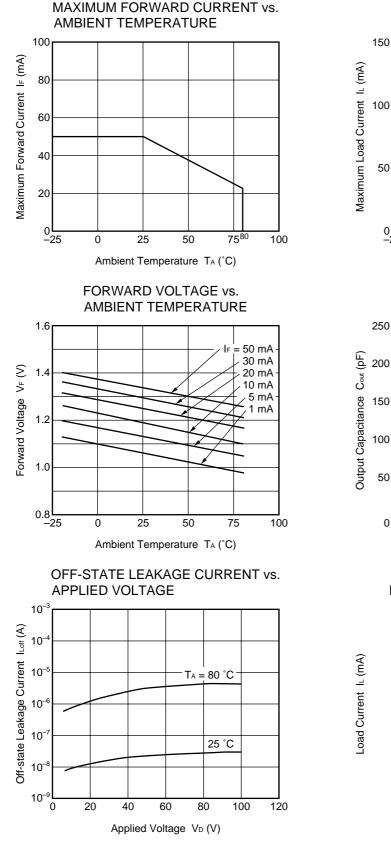
# \* ELECTRICAL CHARACTERISTICS (TA = 25 °C)

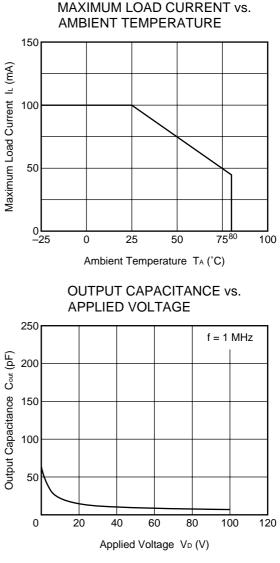
	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 10 mA		1.2	1.4	V
	Reverse Current	Ir	V <sub>R</sub> = 5 V			5.0	μA
MOS FET	Off-state Leakage Current	Loff	V <sub>D</sub> = 100 V		0.03	1.0	μA
	Output Capacitance	Cout	V <sub>D</sub> = 0 V, f = 1 MHz		57		pF/ch
Coupled	LED On-state Current	IFon	I∟ = 100 mA			2.0	mA
	On-state Resistance	Ron1	I⊧ = 10 mA, I∟ = 10 mA		3.0	6.0	Ω
		Ron2	$I_F = 10 \text{ mA}, I_L = 100 \text{ mA}, t \le 10 \text{ ms}$				
	Turn-on Time <sup>*1</sup>	ton	IF = 10 mA, Vo = 5 V, PW $\ge$ 10 ms		0.1	0.4	ms
	Turn-off Time <sup>*1</sup>	toff			0.03	0.2	
	Isolation Resistance	Ri-o	VI-O = 1.0 kVDC	10°			Ω
	Isolation Capacitance	CI-0	V = 0 V, f = 1 MHz		1.1		pF/ch

\*1 Test Circuit for Switching Time

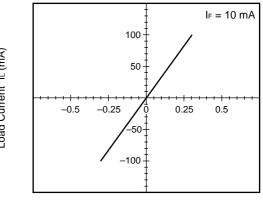


## ★ TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise specified)



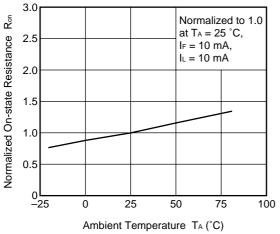


#### LOAD CURRENT vs. LOAD VOLTAGE

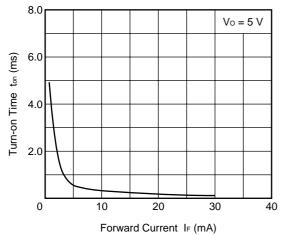


Load Voltage VL (V)

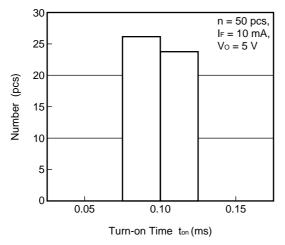
# NORMALIZED ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



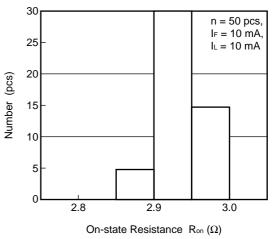
# TURN-ON TIME vs. FORWARD CURRENT



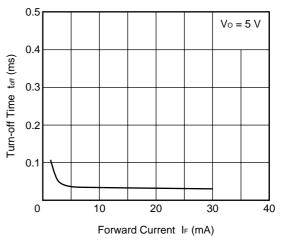
#### TURN-ON TIME DISTRIBUTION



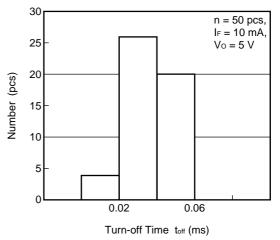
## ON-STATE RESISTANCE DISTRIBUTION

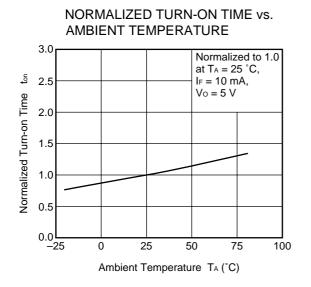


#### TURN-OFF TIME vs. FORWARD CURRENT

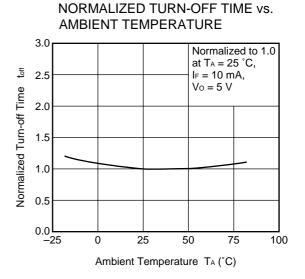


# TURN-OFF TIME DISTRIBUTION

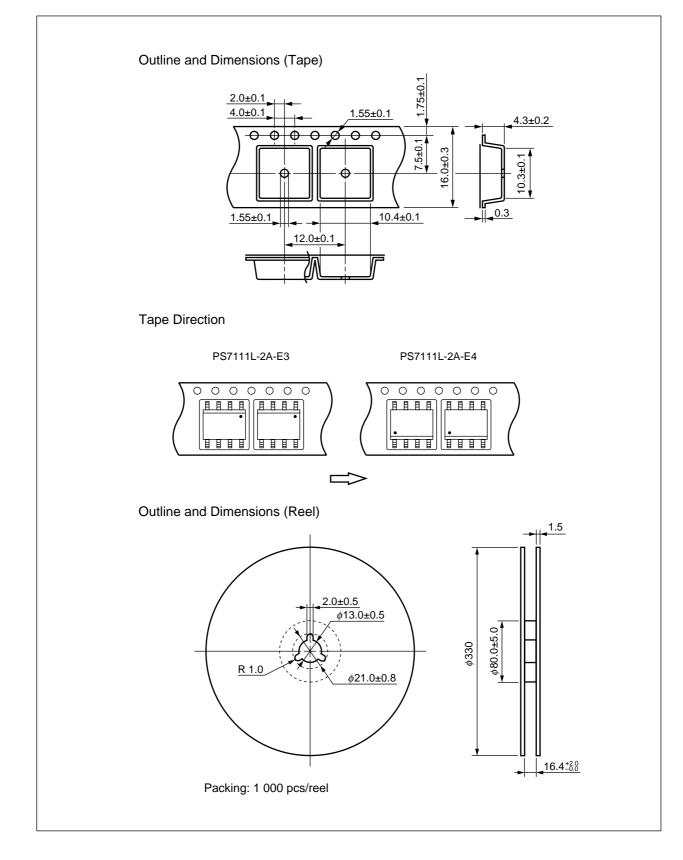




**Remark** The graphs indicate nominal characteristics.



# **\*** TAPING SPECIFICATIONS (in millimeters)



# **RECOMMENDED SOLDERING CONDITIONS**

# (1) Infrared reflow soldering

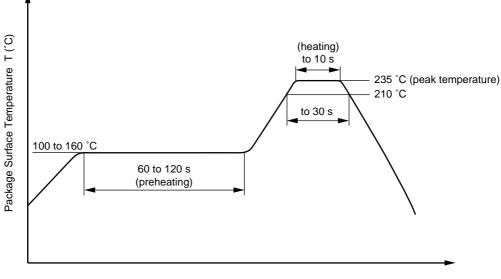
- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C
- Number of reflows
- Flux

Two Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt % is recommended.)

#### Recommended Temperature Profile of Infrared Reflow

30 seconds or less





#### (2) Dip soldering

#### • Temperature 260 °C or below (molten solder temperature)

- Time
  - e 10 seconds or less
- Number of times One
- Flux

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

# (3) Cautions

• Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

[MEMO]

[MEMO]

# CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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